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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	1152
Number of Logic Elements/Cells	11520
Total RAM Bits	147456
Number of I/O	408
Number of Gates	728000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k300efc672-3

- Flexible clock management circuitry with up to four phase-locked loops (PLLs)
 - Built-in low-skew clock tree
 - Up to eight global clock signals
 - ClockLock[®] feature reducing clock delay and skew
 - ClockBoost[®] feature providing clock multiplication and division
 - ClockShift[™] programmable clock phase and delay shifting
- Powerful I/O features
 - Compliant with peripheral component interconnect Special Interest Group (PCI SIG) *PCI Local Bus Specification, Revision 2.2* for 3.3-V operation at 33 or 66 MHz and 32 or 64 bits
 - Support for high-speed external memories, including DDR SDRAM and ZBT SRAM (ZBT is a trademark of Integrated Device Technology, Inc.)
 - Bidirectional I/O performance ($t_{CO} + t_{SU}$) up to 250 MHz
 - LVDS performance up to 840 Mbits per channel
 - Direct connection from I/O pins to local interconnect providing fast t_{CO} and t_{SU} times for complex logic
 - MultiVolt I/O interface support to interface with 1.8-V, 2.5-V, 3.3-V, and 5.0-V devices (see [Table 3](#))
 - Programmable clamp to V_{CCIO}
 - Individual tri-state output enable control for each pin
 - Programmable output slew-rate control to reduce switching noise
 - Support for advanced I/O standards, including low-voltage differential signaling (LVDS), LVPECL, PCI-X, AGP, CTT, stub-series terminated logic (SSTL-3 and SSTL-2), Gunning transceiver logic plus (GTL+), and high-speed terminated logic (HSTL Class I)
 - Pull-up on I/O pins before and during configuration
- Advanced interconnect structure
 - Four-level hierarchical FastTrack[®] Interconnect structure providing fast, predictable interconnect delays
 - Dedicated carry chain that implements arithmetic functions such as fast adders, counters, and comparators (automatically used by software tools and megafunctions)
 - Dedicated cascade chain that implements high-speed, high-fan-in logic functions (automatically used by software tools and megafunctions)
 - Interleaved local interconnect allows one LE to drive 29 other LEs through the fast local interconnect
- Advanced packaging options
 - Available in a variety of packages with 144 to 1,020 pins (see [Tables 4 through 7](#))
 - FineLine BGA[®] packages maximize board space efficiency
- Advanced software support
 - Software design support and automatic place-and-route provided by the Altera[®] Quartus[®] II development system for

Logic Array Block

Each LAB consists of 10 LEs, the LEs' associated carry and cascade chains, LAB control signals, and the local interconnect. The local interconnect transfers signals between LEs in the same or adjacent LABs, IOEs, or ESBs. The Quartus II Compiler places associated logic within an LAB or adjacent LABs, allowing the use of a fast local interconnect for high performance. Figure 3 shows the APEX 20K LAB.

APEX 20K devices use an interleaved LAB structure. This structure allows each LE to drive two local interconnect areas. This feature minimizes use of the MegaLAB and FastTrack interconnect, providing higher performance and flexibility. Each LE can drive 29 other LEs through the fast local interconnect.

Figure 3. LAB Structure

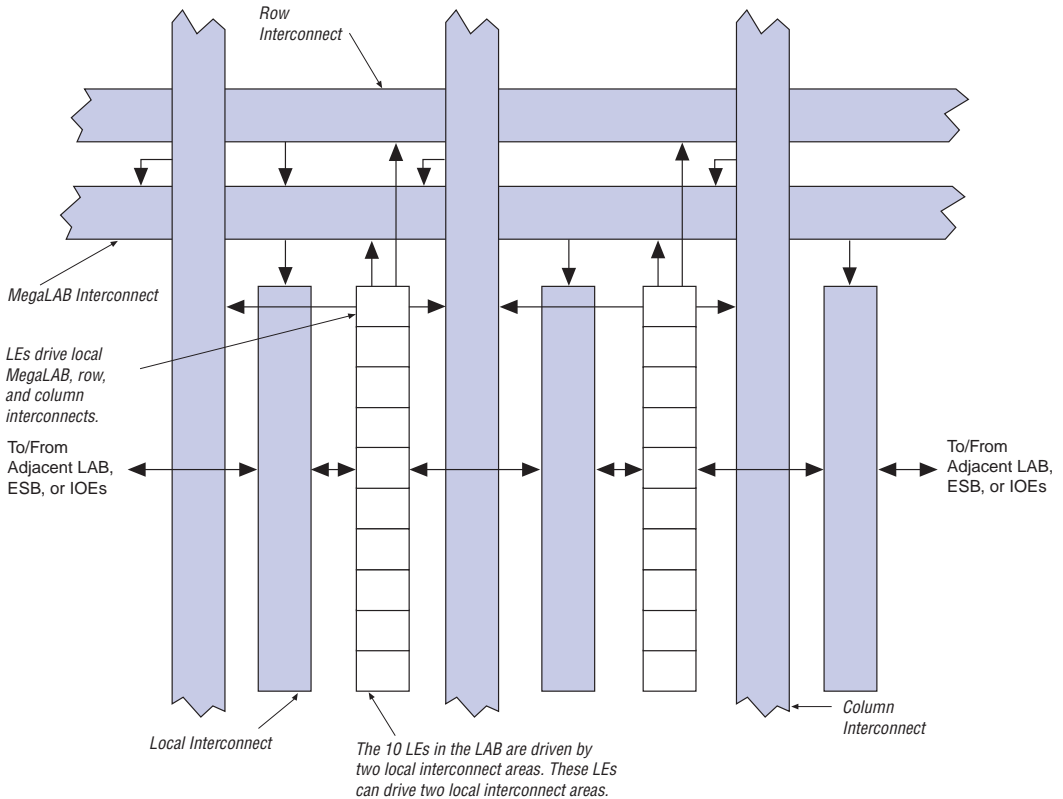
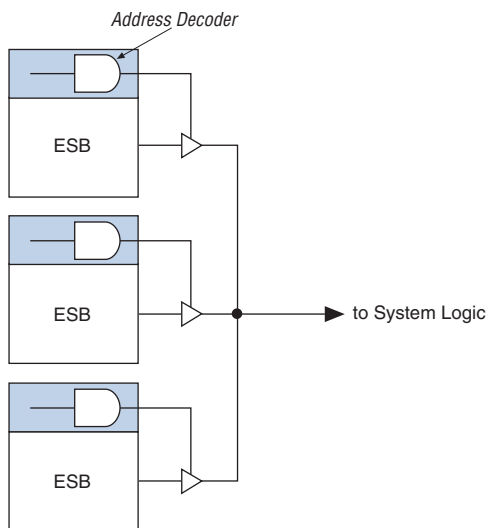


Figure 18. Deep Memory Block Implemented with Multiple ESBs

The ESB implements two forms of dual-port memory: read/write clock mode and input/output clock mode. The ESB can also be used for bidirectional, dual-port memory applications in which two ports read or write simultaneously. To implement this type of dual-port memory, two or four ESBs are used to support two simultaneous reads or writes. This functionality is shown in [Figure 19](#).

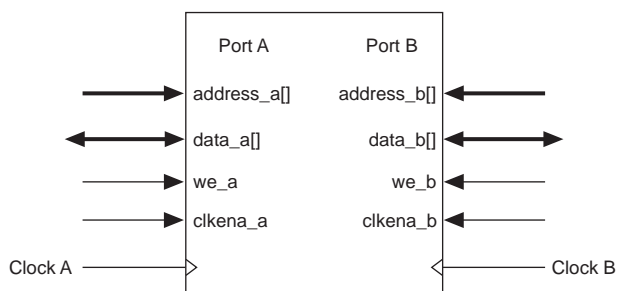
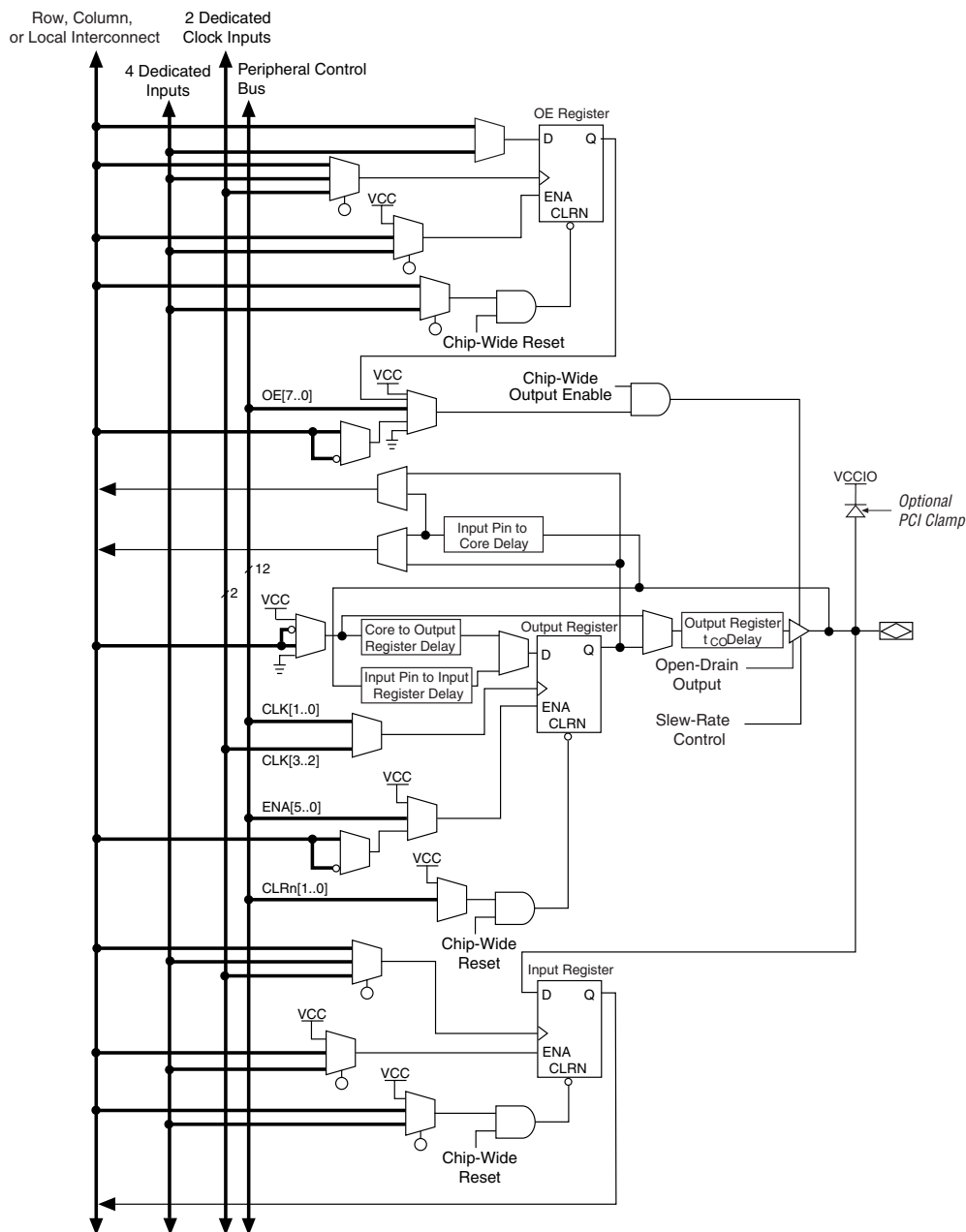
Figure 19. APEX 20K ESB Implementing Dual-Port RAM

Figure 25. APEX 20K Bidirectional I/O Registers *Note (1)*



Note to Figure 25:

(1) The output enable and input registers are LE registers in the LAB adjacent to the bidirectional pin.

APEX 20KE devices include an enhanced IOE, which drives the FastRow interconnect. The FastRow interconnect connects a column I/O pin directly to the LAB local interconnect within two MegaLAB structures. This feature provides fast setup times for pins that drive high fan-outs with complex logic, such as PCI designs. For fast bidirectional I/O timing, LE registers using local routing can improve setup times and OE timing. The APEX 20KE IOE also includes direct support for open-drain operation, giving faster clock-to-output for open-drain signals. Some programmable delays in the APEX 20KE IOE offer multiple levels of delay to fine-tune setup and hold time requirements. The Quartus II software compiler can set these delays automatically to minimize setup time while providing a zero hold time.

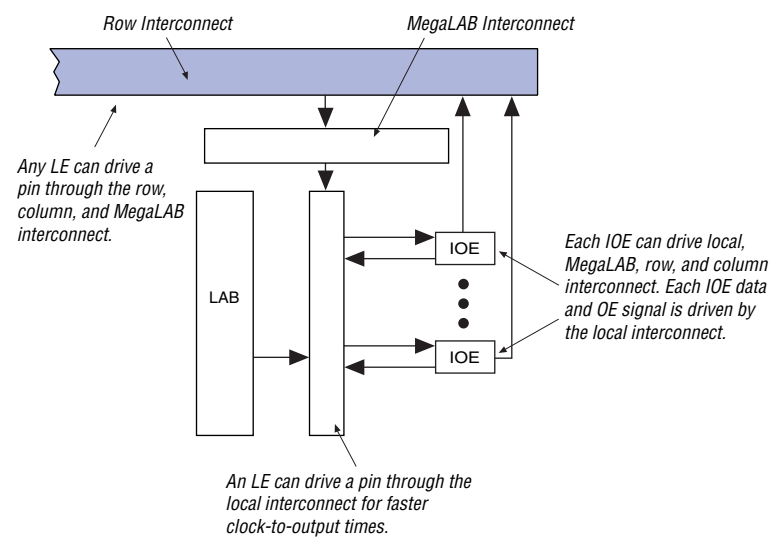
Table 11 describes the APEX 20KE programmable delays and their logic options in the Quartus II software.

Table 11. APEX 20KE Programmable Delay Chains	
Programmable Delays	Quartus II Logic Option
Input Pin to Core Delay	Decrease input delay to internal cells
Input Pin to Input Register Delay	Decrease input delay to input registers
Core to Output Register Delay	Decrease input delay to output register
Output Register t_{CO} Delay	Increase delay to output pin
Clock Enable Delay	Increase clock enable delay

The register in the APEX 20KE IOE can be programmed to power-up high or low after configuration is complete. If it is programmed to power-up low, an asynchronous clear can control the register. If it is programmed to power-up high, an asynchronous preset can control the register. **Figure 26** shows how fast bidirectional I/O pins are implemented in APEX 20KE devices. This feature is useful for cases where the APEX 20KE device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Each IOE drives a row, column, MegaLAB, or local interconnect when used as an input or bidirectional pin. A row IOE can drive a local, MegaLAB, row, and column interconnect; a column IOE can drive the column interconnect. **Figure 27** shows how a row IOE connects to the interconnect.

Figure 27. Row IOE Connection to the Interconnect



MultiVolt I/O Interface

Under hot socketing conditions, APEX 20KE devices will not sustain any damage, but the I/O pins will drive out.

The APEX device architecture supports the MultiVolt I/O interface feature, which allows APEX devices in all packages to interface with systems of different supply voltages. The devices have one set of VCC pins for internal operation and input buffers (VCCINT), and another set for I/O output drivers (VCCIO).

The APEX 20K VCCINT pins must always be connected to a 2.5 V power supply. With a 2.5-V VCCINT level, input pins are 2.5-V, 3.3-V, and 5.0-V tolerant. The VCCIO pins can be connected to either a 2.5-V or 3.3-V power supply, depending on the output requirements. When VCCIO pins are connected to a 2.5-V power supply, the output levels are compatible with 2.5-V systems. When the VCCIO pins are connected to a 3.3-V power supply, the output high is 3.3 V and is compatible with 3.3-V or 5.0-V systems.

Table 12 summarizes 5.0-V tolerant APEX 20K MultiVolt I/O support.

Table 12. 5.0-V Tolerant APEX 20K MultiVolt I/O Support						
V_{CCIO} (V)	Input Signals (V)			Output Signals (V)		
	2.5	3.3	5.0	2.5	3.3	5.0
2.5	✓	✓(1)	✓(1)	✓		
3.3	✓	✓	✓(1)	✓(2)	✓	✓

Notes to Table 12:

- (1) The PCI clamping diode must be disabled to drive an input with voltages higher than V_{CCIO}.
- (2) When V_{CCIO} = 3.3 V, an APEX 20K device can drive a 2.5-V device with 3.3-V tolerant inputs.

Open-drain output pins on 5.0-V tolerant APEX 20K devices (with a pull-up resistor to the 5.0-V supply) can drive 5.0-V CMOS input pins that require a V_{IH} of 3.5 V. When the pin is inactive, the trace will be pulled up to 5.0 V by the resistor. The open-drain pin will only drive low or tri-state; it will never drive high. The rise time is dependent on the value of the pull-up resistor and load impedance. The I_{OL} current specification should be considered when selecting a pull-up resistor.

APEX 20KE devices also support the MultiVolt I/O interface feature. The APEX 20KE VCCINT pins must always be connected to a 1.8-V power supply. With a 1.8-V VCCINT level, input pins are 1.8-V, 2.5-V, and 3.3-V tolerant. The VCCIO pins can be connected to either a 1.8-V, 2.5-V, or 3.3-V power supply, depending on the I/O standard requirements. When the VCCIO pins are connected to a 1.8-V power supply, the output levels are compatible with 1.8-V systems. When VCCIO pins are connected to a 2.5-V power supply, the output levels are compatible with 2.5-V systems. When VCCIO pins are connected to a 3.3-V power supply, the output high is 3.3 V and compatible with 3.3-V or 5.0-V systems. An APEX 20KE device is 5.0-V tolerant with the addition of a resistor.

Table 13 summarizes APEX 20KE MultiVolt I/O support.

Table 13. APEX 20KE MultiVolt I/O Support <i>Note (1)</i>								
V _{CCIO} (V)	Input Signals (V)				Output Signals (V)			
	1.8	2.5	3.3	5.0	1.8	2.5	3.3	5.0
1.8	✓	✓	✓		✓			
2.5	✓	✓	✓			✓		
3.3	✓	✓	✓	(2)			✓(3)	

Notes to Table 13:

- (1) The PCI clamping diode must be disabled to drive an input with voltages higher than V_{CCIO}, except for the 5.0-V input case.
- (2) An APEX 20KE device can be made 5.0-V tolerant with the addition of an external resistor. You also need a PCI clamp and series resistor.
- (3) When V_{CCIO} = 3.3 V, an APEX 20KE device can drive a 2.5-V device with 3.3-V tolerant inputs.

ClockLock & ClockBoost Features

APEX 20K devices support the ClockLock and ClockBoost clock management features, which are implemented with PLLs. The ClockLock circuitry uses a synchronizing PLL that reduces the clock delay and skew within a device. This reduction minimizes clock-to-output and setup times while maintaining zero hold times. The ClockBoost circuitry, which provides a clock multiplier, allows the designer to enhance device area efficiency by sharing resources within the device. The ClockBoost circuitry allows the designer to distribute a low-speed clock and multiply that clock on-device. APEX 20K devices include a high-speed clock tree; unlike ASICs, the user does not have to design and optimize the clock tree. The ClockLock and ClockBoost features work in conjunction with the APEX 20K device's high-speed clock to provide significant improvements in system performance and band-width. Devices with an X-suffix on the ordering code include the ClockLock circuit.

The ClockLock and ClockBoost features in APEX 20K devices are enabled through the Quartus II software. External devices are not required to use these features.

The APEX 20K device instruction register length is 10 bits. The APEX 20K device USERCODE register length is 32 bits. [Tables 20 and 21](#) show the boundary-scan register length and device IDCODE information for APEX 20K devices.

Table 20. APEX 20K Boundary-Scan Register Length

Device	Boundary-Scan Register Length
EP20K30E	420
EP20K60E	624
EP20K100	786
EP20K100E	774
EP20K160E	984
EP20K200	1,176
EP20K200E	1,164
EP20K300E	1,266
EP20K400	1,536
EP20K400E	1,506
EP20K600E	1,806
EP20K1000E	2,190
EP20K1500E	1 (1)

Note to [Table 20](#):

- (1) This device does not support JTAG boundary scan testing.

Table 21. 32-Bit APEX 20K Device IDCODE

Device	IDCODE (32 Bits) ⁽¹⁾			
	Version (4 Bits)	Part Number (16 Bits)	Manufacturer Identity (11 Bits)	1 (1 Bit) ⁽²⁾
EP20K30E	0000	1000 0000 0011 0000	000 0110 1110	1
EP20K60E	0000	1000 0000 0110 0000	000 0110 1110	1
EP20K100	0000	0000 0100 0001 0110	000 0110 1110	1
EP20K100E	0000	1000 0001 0000 0000	000 0110 1110	1
EP20K160E	0000	1000 0001 0110 0000	000 0110 1110	1
EP20K200	0000	0000 1000 0011 0010	000 0110 1110	1
EP20K200E	0000	1000 0010 0000 0000	000 0110 1110	1
EP20K300E	0000	1000 0011 0000 0000	000 0110 1110	1
EP20K400	0000	0001 0110 0110 0100	000 0110 1110	1
EP20K400E	0000	1000 0100 0000 0000	000 0110 1110	1
EP20K600E	0000	1000 0110 0000 0000	000 0110 1110	1
EP20K1000E	0000	1001 0000 0000 0000	000 0110 1110	1

Notes to Table 21:

- (1) The most significant bit (MSB) is on the left.
 (2) The IDCODE's least significant bit (LSB) is always 1.

Figure 31 shows the timing requirements for the JTAG signals.

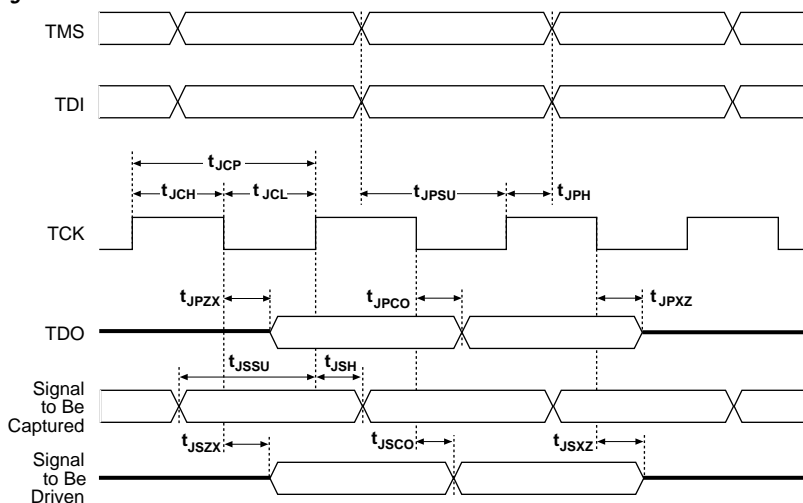
Figure 31. APEX 20K JTAG Waveforms

Table 24. APEX 20K 5.0-V Tolerant Device Recommended Operating Conditions *Note (2)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	(4), (5)	2.375 (2.375)	2.625 (2.625)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	(4), (5)	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	(4), (5)	2.375 (2.375)	2.625 (2.625)	V
V_I	Input voltage	(3), (6)	−0.5	5.75	V
V_O	Output voltage		0	V_{CCIO}	V
T_J	Junction temperature	For commercial use	0	85	° C
		For industrial use	−40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Table 25. APEX 20K 5.0-V Tolerant Device DC Operating Conditions (Part 1 of 2) *Notes (2), (7), (8)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		1.7, $0.5 \times V_{CCIO}$ (9)		5.75	V
V_{IL}	Low-level input voltage		−0.5		$0.8, 0.3 \times V_{CCIO}$ (9)	V
V_{OH}	3.3-V high-level TTL output voltage	$I_{OH} = -8$ mA DC, $V_{CCIO} = 3.00$ V (10)	2.4			V
	3.3-V high-level CMOS output voltage	$I_{OH} = -0.1$ mA DC, $V_{CCIO} = 3.00$ V (10)	$V_{CCIO} - 0.2$			V
	3.3-V high-level PCI output voltage	$I_{OH} = -0.5$ mA DC, $V_{CCIO} = 3.00$ to 3.60 V (10)	$0.9 \times V_{CCIO}$			V
	2.5-V high-level output voltage	$I_{OH} = -0.1$ mA DC, $V_{CCIO} = 2.30$ V (10)	2.1			V
		$I_{OH} = -1$ mA DC, $V_{CCIO} = 2.30$ V (10)	2.0			V
		$I_{OH} = -2$ mA DC, $V_{CCIO} = 2.30$ V (10)	1.7			V

Table 26. APEX 20K 5.0-V Tolerant Device Capacitance *Notes (2), (14)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	$V_{IN} = 0\text{ V}$, $f = 1.0\text{ MHz}$		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	$V_{IN} = 0\text{ V}$, $f = 1.0\text{ MHz}$		12	pF
C_{OUT}	Output capacitance	$V_{OUT} = 0\text{ V}$, $f = 1.0\text{ MHz}$		8	pF

Notes to Tables 23 through 26:

- (1) See the *Operating Requirements for Altera Devices Data Sheet*.
- (2) All APEX 20K devices are 5.0-V tolerant.
- (3) Minimum DC input is -0.5 V . During transitions, the inputs may undershoot to -2.0 V or overshoot to 5.75 V for input currents less than 100 mA and periods shorter than 20 ns .
- (4) Numbers in parentheses are for industrial-temperature-range devices.
- (5) Maximum V_{CC} rise time is 100 ms , and V_{CC} must rise monotonically.
- (6) All pins, including dedicated inputs, clock I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
- (7) Typical values are for $T_A = 25^\circ\text{C}$, $V_{CCINT} = 2.5\text{ V}$, and $V_{CCIO} = 2.5\text{ or }3.3\text{ V}$.
- (8) These values are specified in the APEX 20K device recommended operating conditions, shown in Table 26 on page 62.
- (9) The APEX 20K input buffers are compatible with 2.5-V and 3.3-V (LVTTTL and LVC MOS) signals. Additionally, the input buffers are 3.3-V PCI compliant when V_{CCIO} and V_{CCINT} meet the relationship shown in Figure 33 on page 68.
- (10) The I_{OH} parameter refers to high-level TTL, PCI or CMOS output current.
- (11) The I_{OL} parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
- (12) This value is specified for normal device operation. The value may vary during power-up.
- (13) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO} .
- (14) Capacitance is sample-tested only.

Tables 27 through 30 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 1.8-V APEX 20KE devices.

Table 27. APEX 20KE Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground (2)	-0.5	2.5	V
V_{CCIO}			-0.5	4.6	V
V_I			-0.5	4.6	V
I_{OUT}	DC output current, per pin		-25	25	mA
T_{STG}	Storage temperature	No bias	-65	150	$^\circ\text{C}$
T_{AMB}	Ambient temperature	Under bias	-65	135	$^\circ\text{C}$
T_J	Junction temperature	PQFP, RQFP, TQFP, and BGA packages, under bias		135	$^\circ\text{C}$
		Ceramic PGA packages, under bias		150	$^\circ\text{C}$

Table 28. APEX 20KE Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	(3), (4)	1.71 (1.71)	1.89 (1.89)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	(3), (4)	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	(3), (4)	2.375 (2.375)	2.625 (2.625)	V
	Supply voltage for output buffers, 1.8-V operation	(3), (4)	1.71 (1.71)	1.89 (1.89)	V
V_I	Input voltage	(5), (6)	−0.5	4.0	V
V_O	Output voltage		0	V_{CCIO}	V
T_J	Junction temperature	For commercial use	0	85	°C
		For industrial use	−40	100	°C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Table 29. APEX 20KE Device DC Operating Conditions *Notes (7), (8), (9)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level LVTTTL, CMOS, or 3.3-V PCI input voltage		1.7, $0.5 \times V_{CCIO}$ (10)		4.1	V
V_{IL}	Low-level LVTTTL, CMOS, or 3.3-V PCI input voltage		-0.5		$0.8, 0.3 \times V_{CCIO}$ (10)	V
V_{OH}	3.3-V high-level LVTTTL output voltage	$I_{OH} = -12$ mA DC, $V_{CCIO} = 3.00$ V (11)	2.4			V
	3.3-V high-level LVCMOS output voltage	$I_{OH} = -0.1$ mA DC, $V_{CCIO} = 3.00$ V (11)	$V_{CCIO} - 0.2$			V
	3.3-V high-level PCI output voltage	$I_{OH} = -0.5$ mA DC, $V_{CCIO} = 3.00$ to 3.60 V (11)	$0.9 \times V_{CCIO}$			V
	2.5-V high-level output voltage	$I_{OH} = -0.1$ mA DC, $V_{CCIO} = 2.30$ V (11)	2.1			V
		$I_{OH} = -1$ mA DC, $V_{CCIO} = 2.30$ V (11)	2.0			V
		$I_{OH} = -2$ mA DC, $V_{CCIO} = 2.30$ V (11)	1.7			V
V_{OL}	3.3-V low-level LVTTTL output voltage	$I_{OL} = 12$ mA DC, $V_{CCIO} = 3.00$ V (12)			0.4	V
	3.3-V low-level LVCMOS output voltage	$I_{OL} = 0.1$ mA DC, $V_{CCIO} = 3.00$ V (12)			0.2	V
	3.3-V low-level PCI output voltage	$I_{OL} = 1.5$ mA DC, $V_{CCIO} = 3.00$ to 3.60 V (12)			$0.1 \times V_{CCIO}$	V
	2.5-V low-level output voltage	$I_{OL} = 0.1$ mA DC, $V_{CCIO} = 2.30$ V (12)			0.2	V
		$I_{OL} = 1$ mA DC, $V_{CCIO} = 2.30$ V (12)			0.4	V
		$I_{OL} = 2$ mA DC, $V_{CCIO} = 2.30$ V (12)			0.7	V
I_I	Input pin leakage current	$V_I = 4.1$ to -0.5 V (13)	-10		10	μ A
I_{OZ}	Tri-stated I/O pin leakage current	$V_O = 4.1$ to -0.5 V (13)	-10		10	μ A
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	$V_I =$ ground, no load, no toggling inputs, -1 speed grade		10		mA
		$V_I =$ ground, no load, no toggling inputs, -2, -3 speed grades		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	$V_{CCIO} = 3.0$ V (14)	20		50	k Ω
		$V_{CCIO} = 2.375$ V (14)	30		80	k Ω
		$V_{CCIO} = 1.71$ V (14)	60		150	k Ω

Table 56. EP20K60E t_{MAX} ESB Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.83		2.57		3.79	ns
t_{ESBSRC}		2.46		3.26		4.61	ns
t_{ESBAWC}		3.50		4.90		7.23	ns
t_{ESBSWC}		3.77		4.90		6.79	ns
$t_{ESBWASU}$	1.59		2.23		3.29		ns
t_{ESBWAH}	0.00		0.00		0.00		ns
$t_{ESBWDSU}$	1.75		2.46		3.62		ns
t_{ESBWDH}	0.00		0.00		0.00		ns
$t_{ESBRASU}$	1.76		2.47		3.64		ns
t_{ESBRAH}	0.00		0.00		0.00		ns
$t_{ESBWESU}$	1.68		2.49		3.87		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	0.08		0.43		1.04		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.29		0.72		1.46		ns
$t_{ESBRADDRSU}$	0.36		0.81		1.58		ns
$t_{ESBDATACO1}$		1.06		1.24		1.55	ns
$t_{ESBDATACO2}$		2.39		3.35		4.94	ns
t_{ESBDD}		3.50		4.90		7.23	ns
t_{PD}		1.72		2.41		3.56	ns
$t_{PTERMSU}$	0.99		1.56		2.55		ns
$t_{PTERMCO}$		1.07		1.26		1.08	ns

Table 87. EP20K400E t_{MAX} Routing Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.25		0.25		0.26	ns
t_{F5-20}		1.01		1.12		1.25	ns
t_{F20+}		3.71		3.92		4.17	ns

Table 88. EP20K400E Minimum Pulse Width Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.36		2.22		2.35		ns
t_{CL}	1.36		2.26		2.35		ns
t_{CLRP}	0.18		0.18		0.19		ns
t_{PREP}	0.18		0.18		0.19		ns
t_{ESBCH}	1.36		2.26		2.35		ns
t_{ESBCL}	1.36		2.26		2.35		ns
t_{ESBWP}	1.17		1.38		1.56		ns
t_{ESBRP}	0.94		1.09		1.25		ns

Table 89. EP20K400E External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.51		2.64		2.77		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	5.25	2.00	5.79	2.00	6.32	ns
$t_{INSUPLL}$	3.221		3.38		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.25	0.50	2.45	-	-	ns

Table 90. EP20K400E External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSUBIDIR}}$	2.93		3.23		3.44		ns
t_{INHBIDIR}	0.00		0.00		0.00		ns
$t_{\text{OUTCOBIDIR}}$	2.00	5.25	2.00	5.79	2.00	6.32	ns
t_{XZBIDIR}		5.95		6.77		7.12	ns
t_{ZXBIDIR}		5.95		6.77		7.12	ns
$t_{\text{INSUBIDIRPLL}}$	4.31		4.76		-		ns
$t_{\text{INHBIDIRPLL}}$	0.00		0.00		-		ns
$t_{\text{OUTCOBIDIRPLL}}$	0.50	2.25	0.50	2.45	-	-	ns
$t_{\text{XZBIDIRPLL}}$		2.94		3.43		-	ns
$t_{\text{ZXBIDIRPLL}}$		2.94		3.43		-	ns

Tables 91 through 96 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K600E APEX 20KE devices.

Table 91. EP20K600E f_{MAX} LE Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.16		0.16		0.17		ns
t_{H}	0.29		0.33		0.37		ns
t_{CO}		0.65		0.38		0.49	ns
t_{LUT}		0.70		1.00		1.30	ns

Table 98. EP20K1000E f_{MAX} ESB Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.78		2.02		1.95	ns
t_{ESBSRC}		2.52		2.91		3.14	ns
t_{ESBAWC}		3.52		4.11		4.40	ns
t_{ESBSWC}		3.23		3.84		4.16	ns
$t_{ESBWASU}$	0.62		0.67		0.61		ns
t_{ESBWAH}	0.41		0.55		0.55		ns
$t_{ESBWDSU}$	0.77		0.79		0.81		ns
t_{ESBWDH}	0.41		0.55		0.55		ns
$t_{ESBRASU}$	1.74		1.92		1.85		ns
t_{ESBRAH}	0.00		0.01		0.23		ns
$t_{ESBWESU}$	2.07		2.28		2.41		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	0.25		0.27		0.29		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.11		0.04		0.11		ns
$t_{ESBRADDRSU}$	0.14		0.11		0.16		ns
$t_{ESBDATACO1}$		1.29		1.50		1.63	ns
$t_{ESBDATACO2}$		2.55		2.99		3.22	ns
t_{ESBDD}		3.12		3.57		3.85	ns
t_{PD}		1.84		2.13		2.32	ns
$t_{PTERMSU}$	1.08		1.19		1.32		ns
$t_{PTERMCO}$		1.31		1.53		1.66	ns

Table 102. EP20K1000E External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{\text{INSUBIDIR}}$	3.22		3.33		3.51		ns
t_{INHBIDIR}	0.00		0.00		0.00		ns
$t_{\text{OUTCOBIDIR}}$	2.00	5.75	2.00	6.33	2.00	6.90	ns
t_{XZBIDIR}		6.31		7.09		7.76	ns
t_{ZXBIDIR}		6.31		7.09		7.76	ns
$t_{\text{INSUBIDIRPLL}}$	3.25		3.26				ns
$t_{\text{INHBIDIRPLL}}$	0.00		0.00				ns
$t_{\text{OUTCOBIDIRPLL}}$	0.50	2.25	0.50	2.99			ns
$t_{\text{XZBIDIRPLL}}$		2.81		3.80			ns
$t_{\text{ZXBIDIRPLL}}$		2.81		3.80			ns

Tables 103 through 108 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K1500E APEX 20KE devices.

Table 103. EP20K1500E f_{MAX} LE Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.25		0.25		0.25		ns
t_{H}	0.25		0.25		0.25		ns
t_{CO}		0.28		0.32		0.33	ns
t_{LUT}		0.80		0.95		1.13	ns

Table 106. EP20K1500E Minimum Pulse Width Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{CH}	1.25		1.43		1.67		ns
t _{CL}	1.25		1.43		1.67		ns
t _{CLRP}	0.20		0.20		0.20		ns
t _{PREP}	0.20		0.20		0.20		ns
t _{ESBCH}	1.25		1.43		1.67		ns
t _{ESBCL}	1.25		1.43		1.67		ns
t _{ESBWP}	1.28		1.51		1.65		ns
t _{ESBRP}	1.11		1.29		1.41		ns

Table 107. EP20K1500E External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{INSU}	3.09		3.30		3.58		ns
t _{INH}	0.00		0.00		0.00		ns
t _{OUTCO}	2.00	6.18	2.00	6.81	2.00	7.36	ns
t _{INSUPLL}	1.94		2.08		-		ns
t _{INHPLL}	0.00		0.00		-		ns
t _{OUTCOPLL}	0.50	2.67	0.50	2.99	-	-	ns